

Supporting Information

Local geometric and electronic structures of gasochromic VO_x films

Wei-Luen Jang¹, Yang-Ming Lu², Chi-Liang Chen³, Ying-Rui Lu^{1,4}, Chung-Li Dong^{1,*},
Ping-Hung Hsieh⁵, Weng-Sing Hwang⁵, Jeng-Lung Chen¹, Jing-Ming Chen¹,
Ting-Shan Chan¹, Jyh-Fu Lee¹, and Wu-Ching Chou⁶

¹ National Synchrotron Radiation Research Center, Hsinchu 30076, Taiwan

² Department of Electrical Engineering, National University of Tainan, Tainan 70005,
Taiwan

³ Institute of Physics, Academia Sinica, Taipei 11529, Taiwan

⁴ Program for Science and Technology of Accelerator Light Source, National Chiao
Tung University, Hsinchu 30010, Taiwan

⁵ Department of Materials Science and Engineering, National Cheng Kung
University, Tainan 70101, Taiwan

⁶ Department of Electrophysics, National Chiao Tung University, Hsinchu 30010,
Taiwan

Figure S1. XAS spectra of V L_{2,3}-edge and O K-edge of as-deposited and annealed VO_x films (blue and red lines represent two measurements) and standard VO₂ and V₂O₅ samples (black lines).

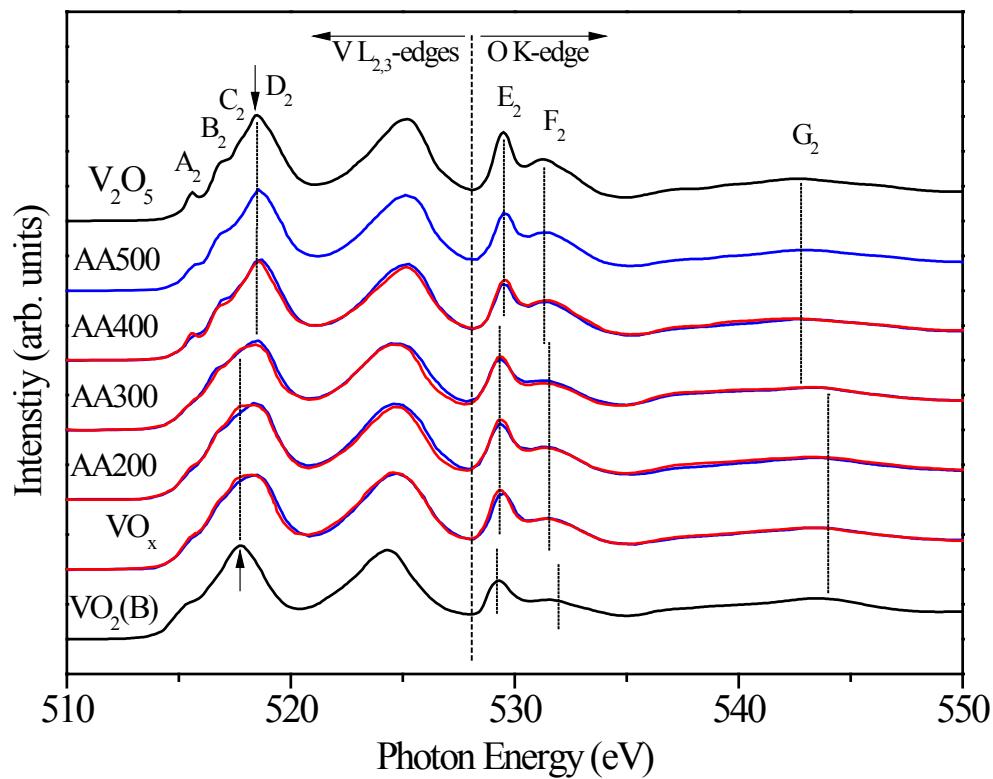


Figure S2. V L_{2,3}-edge and O K-edge XAS of VO_x films in bleached states (black lines) and colored states (red lines).

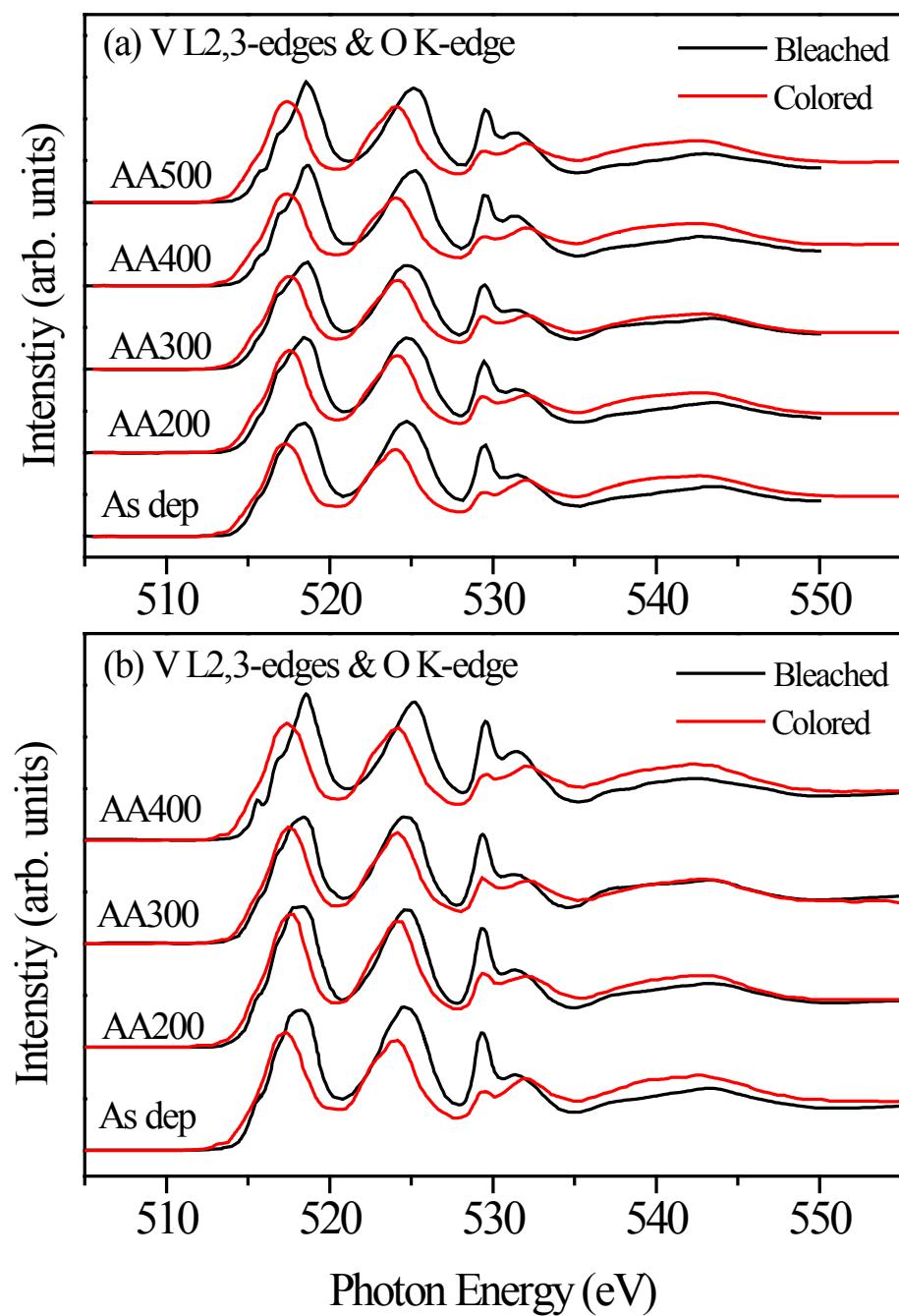


Figure 3S. V K-edge XAS spectra of films before (black lines) and after (red lines) gasochromic reaction from two measurements.

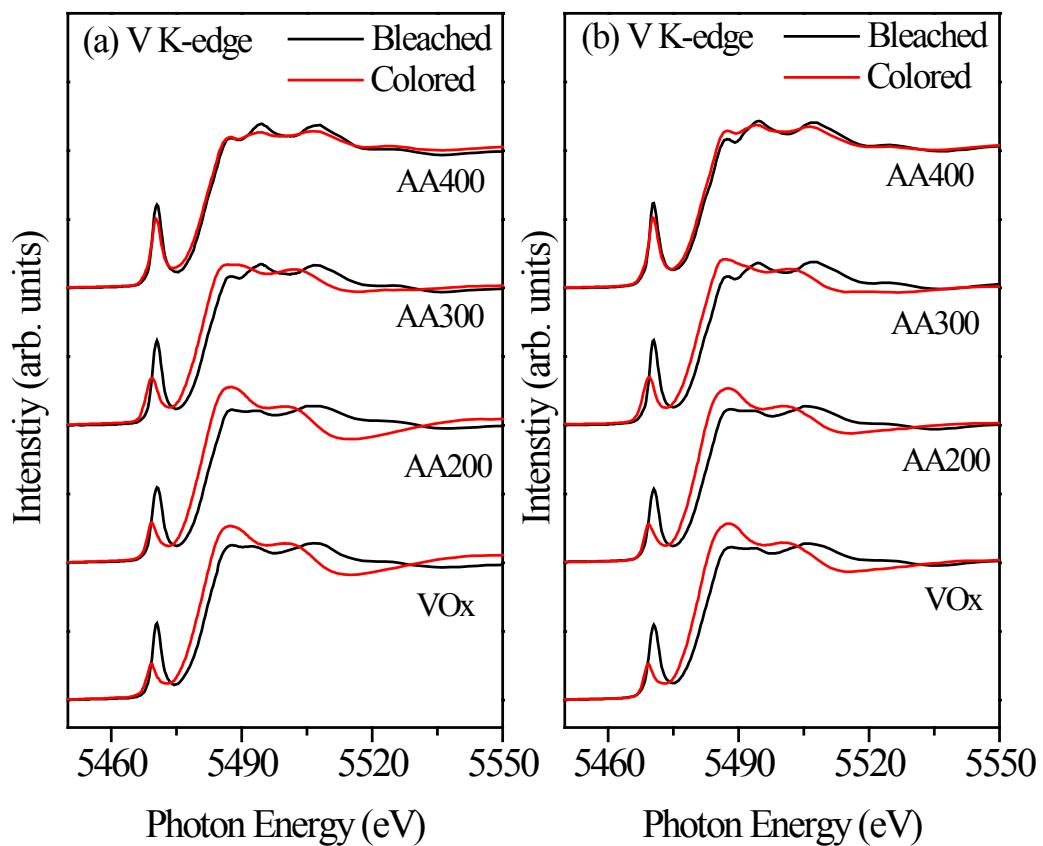


Figure S4. Polarized V K-edge XAS of (a) as-deposited VO_x and (b) V₂O₅ xerogel for incidence angles of 20°, 45°, and 90°.

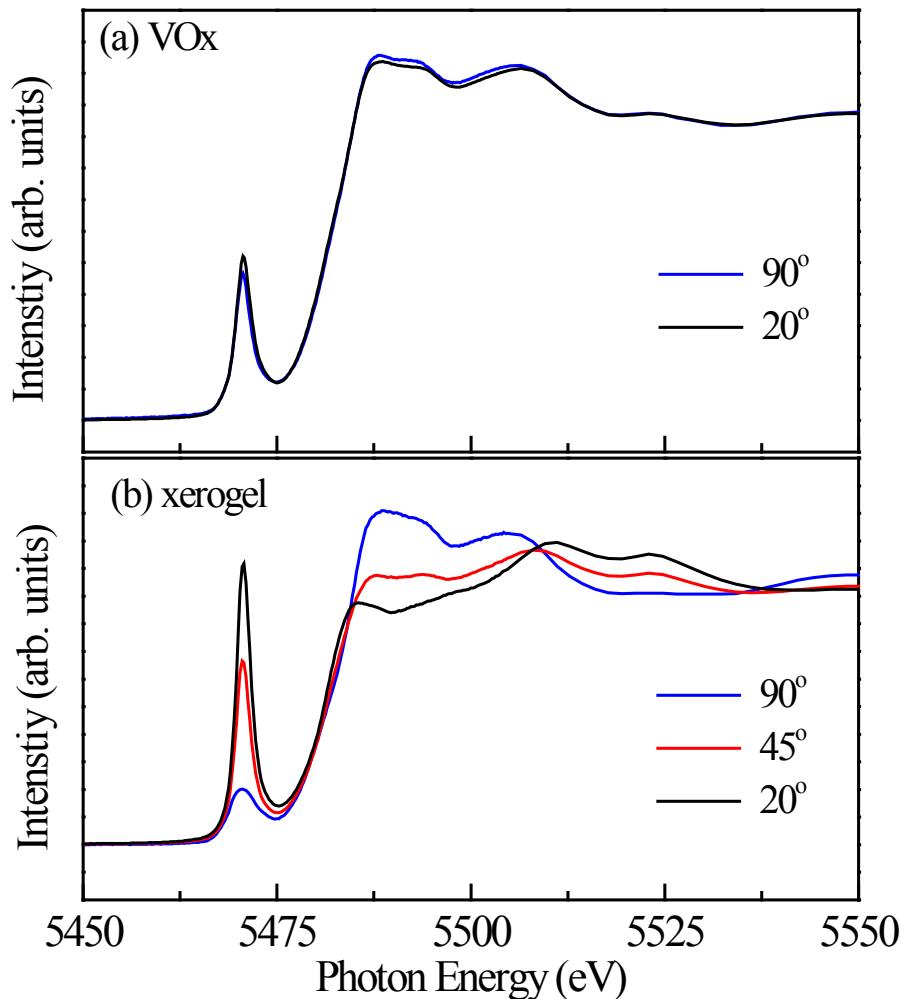


Figure 5S. Polarized V K-edge XAS spectra of hydrogen-saturated VO_x for incidence angles of 20° and 90°.

